



**SCHOTTKY DIE SPECIFICATION**

TYPE: MBR2100

General Description: 100 V 2 A (Low Ir)

Single Anode

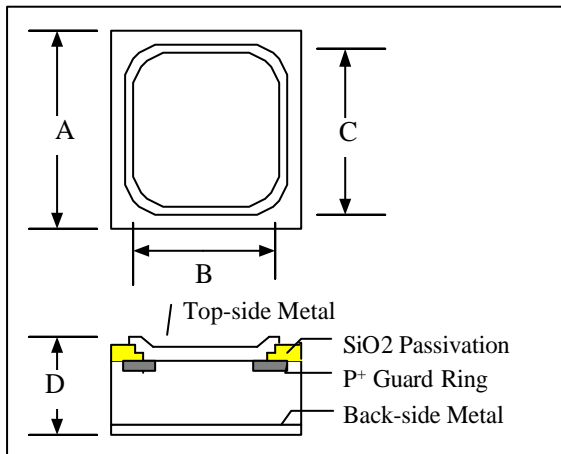
ELECTRICAL CHARACTERISTICS	SYM	Spec. Limit	Die Sort	UNIT
DC Blocking Voltage: Ir=1mA(for wafer form)	VRRM	100	105	Volt
Ir=0.5mA (for dice form)				
Average Rectified Forward Current	IFAV	2		Amp
Maximum Instantaneous Forward Voltage				
@ 1 Amperes, Ta=25°C	VF MAX	0.74	0.73	Volt
@ 2 Amperes, 25°C		0.82	0.81	
Maximum Instantaneous Reverse Voltage				
VR= 100 Volt, Ta=25°C	IR MAX	0.1	0.09	mA
Maximum Junction Capacitance @ 0V, 1MHZ	Cj MAX			pF
<b>MAXIMUM RATINGS</b>				
Nonrepetitive Peak Surge Current	IFSM	50		Amp
Operating Junction Temperature	Tj	-65 to +125		°C
Storage Temperatures	TSTG	-65 to +125		°C

Specification apply to die only. Actual performance may degrade when assembled.

MEMT does not guarantee device performance after assembly.

Data sheet information is subjected to change without notice.

**DICE OUTLINE DRAWING**



DIM	ITEM	um <sup>2</sup>	Mil <sup>2</sup>
A	Die Size	1245	49.01
B	Top Metal Pad Size	1025	40.3
C	Passivation Seal	1203	47.3
D	Thickness (Min)	254	10
	Thickness (Max)	305	12

**PS:**

(1)Cutting street width is around 80um(3.14mil).

(2)Both of top-side and back-side metals are Ti/Ni/Ag.